

6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com

RADIATION HARDENED NPN SILICON SWITCHING TRANSISTOR Qualified per MIL-PRF-19500/255

DEVICES

2N2221A	2N2222A
2N2221AL	2N2222AL
2N2221AUA	2N2222AUA
2N2221AUB	2N2222AUB
2N2221AUBC	2N2222AUBC

LEVELS

JANSM – 3K Rads (Si) JANSD – 10K Rads (Si) JANSP – 30K Rads (Si) JANSL – 50K Rads (Si) JANSR – 100K Rads (Si) JANSF – 300K Rads (Si) JANSG – 500K Rads (Si) JANSH – 1MEG Rads (Si)

ABSOLUTE MAXIMUM RATINGS ($T_c = +25^{\circ}C$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector-Base Voltage	V _{CBO}	75	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current	I _C	800	mAdc
Total Power Dissipation @ $T_A = +25^{\circ}C$			
2N2221A, L2N2222A, L2N2221AUA2N2222AUA2N2221AUB, UBC2N2222AUB, UBC	P _T	0.5 0.65 0.50	W
Operating & Storage Junction Temperature Range	T _{op} , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Parameters / Test Co	Symbol	Max.	Unit	
Thermal Resistance, Ju 2N2221A, L	nction-to-Ambient 2N2222A, L		325	
2N2221A, L 2N2221AUA 2N2221AUB, UBC	2N2222A, L 2N2222AUA 2N2222AUB, UBC	$R_{\theta JA}$	325 210 325	°C/W

1. Derate linearly 3.08 mW/°C above $T_A > +37.5^{\circ}C$

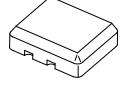
2. Derate linearly 4.76 mW/°C above $T_A > +63.5$ °C



TO-18 (TO-206AA) 2N2221A, 2N2222A



4 PIN 2N2221AUA, 2N2222AUA



3 PIN 2N2221AUB, 2N2222AUB 2N2221AUBC, 2N2222AUBC (UBC = Ceramic Lid Version)



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http://www.microsemi.com

ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}C$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage					
$I_C = 10 mAdc$		V _{(BR)CEO}	50		Vdc
Collector-Base Cutoff Current					
$V_{CB} = 75 V dc$ $V_{CB} = 60 V dc$		I _{CBO}		10 10	μAdc ηAdc
Emitter-Base Cutoff Current					
$V_{EB} = 6.0 V dc$ $V_{EB} = 4.0 V dc$		$I_{\rm EBO}$		10 10	μAdc ηAdc
Collector-Emitter Cutoff Current					
$V_{CE} = 50 V dc$		I _{CES}		50	ηAdc
ON CHARACTERISTICS (3)					
Forward-Current Transfer Ratio					
$I_C = 0.1 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC		30 50		
$I_C = 1.0 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC		35 75	150 325	
$I_C = 10$ mAdc, $V_{CE} = 10$ Vdc	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC	\mathbf{h}_{FE}	40 100		
$I_{C} = 150 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC		40 100	120 300	
$I_C = 500 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC		20 30		
Collector-Emitter Saturation Voltage					
$I_{C} = 150 \text{mAdc}, I_{B} = 15 \text{mAdc}$ $I_{C} = 500 \text{mAdc}, I_{B} = 50 \text{mAdc}$		V _{CE(sat)}		0.3 1.0	Vdc
Base-Emitter Voltage					
$I_{C} = 150 \text{mAdc}, I_{B} = 15 \text{mAdc}$ $I_{C} = 500 \text{mAdc}, I_{B} = 50 \text{mAdc}$		V _{BE(sat)}	0.6	1.2 2.0	Vdc



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit	
Small-Signal Short-Circuit Forward Current Tr					
$I_C = 1.0 \text{mAdc}, V_{CE} = 10 \text{Vdc}, f = 1.0 \text{kHz}$	2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC	\mathbf{h}_{fe}	30 50		
Magnitude of Small–Signal Short-Circuit Forward Current Transfer Ratio					
$I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, $f = 100$ MHz		h _{fe}	2.5		
Output Capacitance					
$V_{CB} = 10 \text{Vdc}, I_E = 0, 100 \text{kHz} \le f \le 1.0 \text{MHz}$		C _{obo}		8.0	pF
Input Capacitance					
$V_{EB}=0.5Vdc,\ I_C=0,\ 100kHz\leq f\leq 1.0MHz$		C_{ibo}		25	pF

SWITCHING CHARACTERISTICS

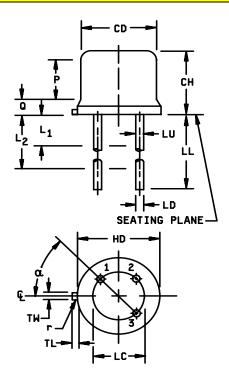
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time See figure 8 of MIL-PRF-19500/255	t _{on}		35	ηs
Turn-Off Time See Figure 9 of MIL-PRF-19500/255	t _{off}		300	ηs

(3) Pulse Test: Pulse Width = $300\mu s$, Duty Cycle $\leq 2.0\%$.



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com

PACKAGE DIMENSIONS



NOTES:

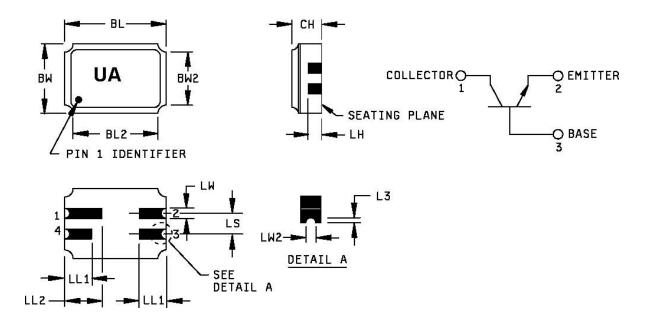
- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TL shall be held for a minimum length of .011 inch (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 7. Dimension LU applies between L_1 and L_2 . Dimension LD applies between L_2 and LL minimum. Diameter is uncontrolled in L_1 and beyond LL minimum.
- 8. All three leads.
- 9. The collector shall be internally connected to the case.
- 10. Dimension r (radius) applies to both inside corners of tab.
- 11. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.
- 12. Lead 1 =emitter, lead 2 =base, lead 3 =collector.
- 13. For L suffix devices, dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max.

Symbol	Inc	hes	Millir	neters	Note
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
СН	.170	.210	4.32	5.33	
HD	.209	.230	5.31	5.84	
LC	.100) TP	2.54	I TP	6
LD	.016	.021	0.41	0.53	7,8
LL	.500	.750	12.70	19.05	7,8,13
LU	.016	.019	0.41	0.48	7,8
L ₁		.050		1.27	7,8
L_2	.250		6.35		7,8
Р	.100		2.54		
Q		.030		0.76	5
TL	.028	.048	0.71	1.22	3,4
TW	.036	.046	0.91	1.17	3
r		.010		0.25	10
α	45° TP		45° TP		6
	1	, 2, 9, 11	, 12, 13		

FIGURE 1. Physical dimensions (similar to TO-18).



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Dimension CH controls the overall package thickness. When a window lid is used, dimension CH must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
- 4. The corner shape (square, notch, radius) may vary at the manufacturer's option, from that shown on the drawing.
- 5. Dimensions LW2 minimum and L3 minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on the bottom two layers, optional on the top ceramic layer.) Dimension LW2 maximum and L3 maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
- 6. The co-planarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed .006 inch (0.15mm) for solder dipped leadless chip carriers.
- 7. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.

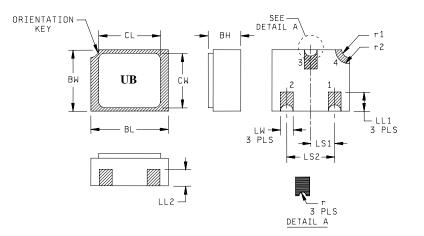
Dimensions					
Symbol	Inc	hes	Millir	neters	Note
	Min	Max	Min	Max	
BL	.215	.225	5.46	5.71	
BL2		.225		5.71	
BW	.145	.155	3.68	3.93	
BW2		.155		3.93	
CH	.061	.075	1.55	1.90	3
L3	.003	.007	0.08	0.18	5
LH	.029	.042	0.74	1.07	
LL1	.032	.048	0.81	1.22	
LL2	.072	.088	1.83	2.23	
LS	.045	.055	1.14	1.39	
LW	.022	.028	0.56	0.71	
LW2	.006	.022	0.15	0.56	5

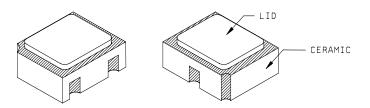
Pin no.	1	2	3	4
Transistor	Collector	Emitter	Base	N/C

FIGURE 2. Physical dimensions, surface mount (UA version).



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com





	Dimensions				
Symbol	Inc	hes	Millir	neters	Note
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	

Dimensions					
Symbol	Inc	hes	Milli	neters	Note
	Min	Max	Min	Max	
LS_1	.036	.040	0.91	1.02	
LS_2	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r ₁		.012		.305	
r ₂		.022		.559	

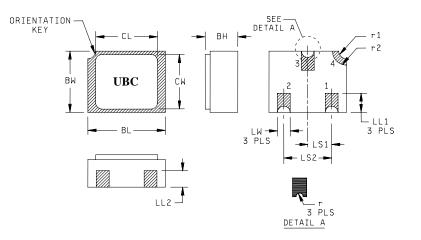
NOTES:

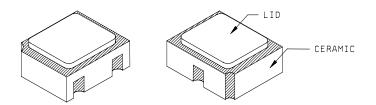
- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Hatched areas on package denote metalized areas.
- 4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
- 5. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 3. Physical dimensions, surface mount (UB version)



6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http: //www.microsemi.com





	Dimensions				
Symbol	Inc	hes	Millir	neters	Note
	Min	Max	Min	Max	
BH	.046	.071	1.17	1.80	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	

	Dimensions				
Symbol	Inches		Millimeters		Note
	Min	Max	Min	Max	
LS_1	.036	.040	0.91	1.02	
LS_2	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r ₁		.012		.305	
r ₂		.022		.559	

NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Hatched areas on package denote metalized areas.
- 4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Connected to the lid braze ring.
- 5. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 4. Physical dimensions, surface mount (UBC version, ceramic lid)

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Microsemi manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15 NTE16001